

## 2D Materials Focus Topic

Room 201B - Session 2D+EM+MI+MN+NS-TuA

## 2D Device Physics and Applications

Moderator: Roland Kawakami, The Ohio State University

2:20pm **2D+EM+MI+MN+NS-TuA1 Spin Relaxation and Proximity Effect in WS<sub>2</sub>/Graphene/Fluorographene Non-local Spin Valves**, Adam Friedman, Laboratory for Physical Sciences; K.M. McCreary, J.T. Robinson, O.M.J. van 't Erve, B.T. Jonker, US Naval Research Laboratory

The mechanisms leading to spin relaxation in graphene and its heterostructures continue to be debated. Control of the spin relaxation in graphene-based structures is necessary to achieve the envisioned utility of graphene in future spintronic devices beyond Moore's law. Proximity induced spin relaxation caused by contact to a high spin-orbit material, such as WS<sub>2</sub>, offers a promising avenue to manipulate the spin lifetime [1]. We demonstrate the operation of WS<sub>2</sub>/graphene/fluorographene non-local spin valves and extract the spin lifetimes for a range of carrier concentrations by Hanle effect measurements. Four-terminal charge transport measurements allow us to calculate the momentum relaxation time as a function of carrier concentration and compare it to the spin lifetime. These data show that the D'yakonov-Perel' mechanism is the dominant spin relaxation mechanism for WS<sub>2</sub>/graphene/fluorographene devices, while, for reference graphene/fluorographene devices, linear scaling between the spin and momentum lifetimes points to spin-flip scattering during strong elastic scattering events where the scattering event is strongly coupled to the electron spin. We attribute the change in spin relaxation type in part with the inclusion of WS<sub>2</sub> as a substrate to proximity induced spin-orbit coupling due to the adjacent WS<sub>2</sub> layer, and we compare our data to the literature.

[1] A.L. Friedman, et al. Carbon 131, 18-25 (2018).

2:40pm **2D+EM+MI+MN+NS-TuA2 Two-dimensional Field-effect Light Emitting Transistors**, Junyoung Kwon, H. Ryu, Yonsei University, Republic of Korea; J.Y. Lee, C.H. Lee, Korea University, Republic of Korea; G.H. Lee, Yonsei University, Republic of Korea

Two dimensional (2D) materials and their heterostructures hold great promises in various applications due to their unique properties and newly discovered physics. Especially, high exciton binding energy and emergence of charged excitons, *i.e.* trions, have shown that 2D semiconductors, such as transition metal dichalcogenides (TMDs), are promising candidates for new concept optoelectronics. Although lots of optoelectronic devices based on the van der Waals heterostructures of 2D materials, such as photodetectors, solar cells, and light emitting devices, have been demonstrated, development of novel optoelectronic devices is still required to fully utilize unique properties of 2D materials and enable multi-functions and versatile applications. Here we demonstrate 2D field-effect light emitting transistors (2D-FELET) consisting of monolayer WSe<sub>2</sub> (light-emitting channel layer) and graphene contacts (tunable carrier injection electrodes). We encapsulated monolayer WSe<sub>2</sub> with two pieces of hexagonal boron nitride and fabricated graphene contacts to two ends of WSe<sub>2</sub>. To selectively inject different types of charge (electrons and holes) at two graphene contacts, two separate top gates on top of WSe<sub>2</sub>-graphene overlap regions were fabricated. By independent modulation of two top gates, Schottky barrier heights for electrons and holes can be tuned, which enables the selective charge injections. When two top gates are oppositely biased, electrons can be injected from one end of WSe<sub>2</sub> channel and holes can be injected from the other end. These opposite charges are recombined at the middle of WSe<sub>2</sub> channel, leading to strong light emission. The performance of the 2D-FELETs is tunable by additional electrical field from back gate. Furthermore, the devices produced in this work can be used as polarity-tunable FETs and photodetectors, simultaneously, which are beneficial for further CMOS integration. Our study shows great potential of 2D-FELETs toward future optoelectronic applications, which request ultra-thinness, transparency, flexibility, high efficiency, multi-functions, and high integration.

3:00pm **2D+EM+MI+MN+NS-TuA3 Quantum Devices with 2D Materials**, H. Overweg, M. Eich, R. Pisoni, T. Ihn, P. Rickhaus, ETH Zurich, Switzerland; Klaus Ensslin, ETH Zürich, Switzerland

INVITED

Quantum dots in graphene have been mostly realized by etching. This leads to localized states at the uncontrolled edges dominating the transport properties of these quantum devices. [1] It is well known that in bilayer graphene gaps can be opened by vertical electrical fields. [2] This approach has been used with limited success to define quantum devices [3]. The

pinch-off characteristics are typically limited by leakage currents often thought to occur at the physical sample edges [4].

Here we demonstrate that electrostatically tunable barriers can be fabricated on bilayer graphene devices with graphite as a back gate. We measure pinch-off resistances exceeding GΩms and observe quantized conduction plateaus for one-dimensional constrictions. [5] With suitable gate arrangements few carrier hole and electron quantum dots can be electrostatically defined. We measure the controlled occupation of quantum dots with single holes and electrons. Four-fold level bunching is observed in Coulomb blockade spectroscopy which is understood in terms of valley and spin states. Magnetic field dependence allows to investigate orbital and spin/valley degrees of freedom.

We further demonstrate quantum devices build on MoS<sub>2</sub>.

1. For a review see Bischoff et al., Applied Physics Reviews 2, 031301 (2015)
2. Oostinga et al., Nat. Materials 7, 151 (2007)
3. Allen et al., Nat. Comm. 3, 934 (2012)
4. [<https://www.nature.com/articles/ncomms14552#auth-1>] et al., Nat. Comm. 8, 14552 (2017)
5. Overweg et al., [<https://arxiv.org/abs/1707.09282>], [<https://arxiv.org/abs/1709.00870>]

4:20pm **2D+EM+MI+MN+NS-TuA7 GaN Microdisk Light-emitting Diode Display Fabricated on Graphene**, Youngbin Choe, K. Chung, K. Lee, M.S. Song, J.B. Park, H. Kim, J.Y. Park, G.-C. Yi, Seoul National University, Republic of Korea

Microdisplay with high resolution, brightness, and efficiency with long-term stability and reliability are highly required for advanced display technologies. Inorganic semiconductor LEDs best suits this purpose because they can emit very high density of light from a small area and they have very high efficiency and long-term stability. To use inorganic LEDs for display applications, various lift-off and transfer techniques of inorganic thin films grown on single crystal substrates, such as sapphire or Si, were developed. However, achieving display devices using inorganic semiconductor thin films is still very challenging because of the limited size and high manufacturing cost of the single crystal substrates, as well as the complicated processes required for lift-off and assembly. To resolve this problem, growths of inorganic semiconductor nanostructures and thin films on graphene substrates have recently been proposed, since graphene has great scalability and extremely thin layered hexagonal lattice structure as an excellent substrate for GaN growth. Moreover, the inorganic semiconductors prepared on large-area graphene can be transferred easily to or grown on elastic substrates to meet the flexibility demand. Here, we suggest a method of fabricating ultrathin, high-resolution inorganic microdisplay based on individually addressable GaN microdisk LED arrays grown on graphene dots.

Here, we report on the fabrication and EL characteristics of ultrathin and individually addressable GaN microdisk LED arrays grown on graphene dots for microdisplay applications. GaN microdisks were prepared by epitaxial lateral overgrowth on patterned graphene microdots on SiO<sub>2</sub>/Si substrates using MOVPE. After preparing the GaN microdisk arrays, *p*-GaN and InGaN/GaN multiple quantum well, and *n*-GaN layers were heteroepitaxially grown on the surface of the GaN microdisks. Ultrathin layers composed of GaN microdisk LED arrays on graphene dot were prepared by coating a polyimide layer and lifting-off the entire layers from the substrate. Then, single-walled carbon nanotubes (SWCNTs)/Ni/Au and SWCNTs/Ti/Au multiple electrode lines were formed on the top and bottom surface of GaN microdisk arrays in an aligned manner and crossing each other. The electrical and optical characteristics of the individually addressable GaN microdisk array on graphene dots were investigated by measuring their *I*-*V* curves and EL characteristics at various bending conditions. We also confirmed that the ultrathin micro-LED display worked reliably under flexible conditions and continuous operation mode.

4:40pm **2D+EM+MI+MN+NS-TuA8 Room Temperature Magnetron Sputtering and Laser Annealing of Ultrathin MoS<sub>2</sub> for Transistor Device Fabrication on Flexible Polymer Substrates**, Benjamin Sirota, University of North Texas; N.R. Glavin, Air Force Research Laboratory; C. Arnold, A.A. Voevodin, University of North Texas

Pulsed magnetron sputtering and subsequent laser annealing provide technologically attractive scalable route for producing two-dimensional (2D) semiconducting grade MoS<sub>2</sub> materials directly on the surface of flexible polymer substrates. In this study the room temperature magnetron sputtering was used to deposit 10 nm thick, amorphous MoS<sub>2</sub> films on

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flexible PDMS as well as rigid SiO<sub>2</sub>/Si substrates. This was followed by 248 nm pulsed laser annealing to produce polycrystalline 2H-MoS<sub>2</sub> over large areas. Raman and XPS analysis confirmed that pulsed laser annealing with about 1 mJ/cm<sup>2</sup> energy density had induced film crystallization from amorphous to hexagonal, while preserving MoS<sub>2</sub> chemical composition, and avoiding formation of oxide phases or damage to the temperature-sensitive polymer surface. Electrical measurements confirmed an order of magnitude improvement in electrical conductivity of the laser annealed films as compared to amorphous MoS<sub>2</sub>. Top-gated field effect transistor (FET) devices with laser annealed sputter grown MoS<sub>2</sub> were directly fabricated on PDMS surfaces. Oxygen substitution of sulfur in sputter deposited MoS<sub>2</sub> and polycrystallinity of the laser annealed 2H-MoS<sub>2</sub> films resulted in low mobility values when compared to mechanically exfoliated and chemical vapor deposition grown single-crystal 2D MoS<sub>2</sub>. However, the described approach is intrinsically scalable and provides a direct growth route for the fabrication of 2D transition metal dichalcogenide semiconducting devices on the surface of flexible and stretchable polymers.

5:00pm **2D+EM+MI+MN+NS-TuA9 Black Phosphorus: Fundamental Properties and Emerging Applications, Han Wang, University of Southern California**  
**INVITED**

In this talk, I will discuss our recent work in developing novel electronic and photonic devices based on the anisotropic properties of black phosphorus (BP) and its isoelectronic materials such as the monochalcogenides of Group IV elements. High mobility, narrow gap BP thin film (0.3 eV in bulk) fill the energy space between zero-gap graphene and large-gap TMDCs, making it a promising material for mid-infrared and long wavelength infrared optoelectronics. Most importantly, its anisotropic nature within the plane of the layers allow for the realization of conceptually new electronic and photonic devices. Here, I will first present our work in understanding the fundamental electronic and optical properties of black phosphorus using a newly developed scanning ultrafast electron microscopy (SUEM) technique and photoluminescence spectroscopy. Our recent the study of bandgap tuning in BP and the demonstration of a polarization sensitive BP mid-IR detector will then be presented. In the second half of my talk, I will discuss our work on developing two dimensional materials based artificial synaptic devices for neuromorphic electronics, including emulating the heterogeneity in synaptic connections using the anisotropic properties of BP and a tunable memristive device as a reconfigurable synapse. I will conclude with remarks on promising future research directions of low-symmetry electronics based on anisotropic 2D materials and how their novel properties is expected to benefit the next-generation electronics and photonics technologies.

5:40pm **2D+EM+MI+MN+NS-TuA11 Patterned Growth of Hybrid Bulk-2D Tungsten Diselenide for Transistor Applications, Quinten Yurek, I. Liao, D. Barroso, A.E. Nguyen, N. Duong, G. Stecklein, L. Bartels, University of California, Riverside**

As device dimensions shrink, surfaces and interfaces between materials make up a larger volume fraction of a device leading to degrading device properties in 3D materials. One solution is to use 2D materials, however these materials introduce additional challenges. For instance, high resistance Schottky barriers and a small number of free charge carriers in comparison to bulk materials. The effective mobility of field effect transistors (FETs) based on two-dimensional (2D) single-layer transition metal dichalcogenide (TMD) films is frequently limited by barriers at the contacts, as opposed to the native properties of the TMD material. Specifically, high resistance Schottky barriers form at the TMD/metal interface because of the film's thinness and resulting small number of carriers. Here we demonstrate a scalable single-step deposition method for nanoscale hybrid 2D/3D TMD structures encoded by lithographic patterning prior to deposition. By confining the metal contact to the bulk regions of WSe<sub>2</sub>, the effective mobility is increased to nearly 100 cm<sup>2</sup>V<sup>-1</sup>s<sup>-1</sup> with an on/off ratio >10<sup>5</sup> for bottom-gated devices (through 300nm of oxide), even for comparatively long channels (>5 microns) and absent other contact optimization. Our process involves lithographic patterning of a hafnium (IV) dioxide film onto the SiO<sub>2</sub>/Si substrate prior to TMD growth. Bulk-like 3D WSe<sub>2</sub> is observed to grow at the location of the hafnia, while 2D single-layer material is grown in regions of bare SiO<sub>2</sub>. Systematic evaluation of transport data allows us to extract Schottky barrier heights and other fundamental properties of our hybrid devices. We demonstrate that this process can be used to create devices with metal/3D TMD contacts, which exhibit a reduced Schottky barrier height, while continuing to use 2D TMD channels, which result in an excellent on-off ratio.

6:00pm **2D+EM+MI+MN+NS-TuA12 Enhanced Ionic Sensitivity in Solution-Gated Graphene-Hexagonal Boron Nitride Heterostructure Field-Effect Transistors, A.D. Radadia, Nowzesh Hasan, B. Hou, A.L. Moore, Louisiana Tech University**

The charge transport in solution-gated graphene devices is affected by the impurities and disorder of the underlying dielectric interface and its interaction with the solution. This paper reports advancement in field-effect ion sensing by fabricating a dielectric isomorph, hexagonal boron nitride between graphene and silicon dioxide of a solution-gated graphene field effect transistor. Ionic sensitivity of Dirac voltage as high as -198 mV/decade for K<sup>+</sup> and -110 mV/decade for Ca<sup>2+</sup> were recorded. Increased transconductance due to increased charge carrier mobility was accompanied with larger ionic sensitivity of the transconductance due to larger ionic sensitivity of the charge carrier mobility. These findings define a standard to construct future graphene devices for biosensing and bioelectronics applications.

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